L	Hits	Search Text	DB	Time stamp
Number			TICD NO.	2003/08/01
1	3	"2002093705"	USPAT;	15:17
			US-PGPUB; EPO; JPO;	15:17
			DERWENT;	
_	1202	(12)	IBM_TDB USPAT;	2003/08/01
2	1383	(silicon or si) same (ge or germanium)	US-PGPUB;	15:18
		same laminat\$4	EPO; JPO;	15:16
			DERWENT;	
			IBM TDB	
_	4.40	(USPAT;	2003/08/01
3	449	(silicon or si) same (ge or germanium)	US-PGPUB;	15:18
		same laminat\$4 same amorphous	EPO; JPO;	12:10
			DERWENT;	
			1	
.	_	(IBM_TDB USPAT;	2003/08/01
4	0			15:18
		same laminat\$4 same amorphous and	US-PGPUB;	12:18
		117/\$.ccls.	EPO; JPO;	
			DERWENT;	1
_	_		IBM_TDB	2002/00/01
5	0		USPAT;	2003/08/01
		same laminat\$4 same amorphous and	US-PGPUB;	15:18
		117/\$4.ccls.	EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	0000 /00 /01
6	85		USPAT;	2003/08/01
		same laminat\$4 same amorphous and	US-PGPUB;	15:20
		257/\$4.ccls.	EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	0000 (00 (01
7	33		USPAT;	2003/08/01
		same laminat\$4 same amorphous and laser	US-PGPUB;	15:25
		near10 (crystalliz\$4 or crystal\$4 or	EPO; JPO;	
		anneal\$4)	DERWENT;	
			IBM_TDB	2002/00/01
8	78	(silicon or si) same (ge or germanium)	USPAT;	2003/08/01 15:26
		same laminat\$4 same amorphous same	US-PGPUB;	13:20
		(crystalliz\$4 or crystal\$4 or anneal\$4)	EPO; JPO;	
			DERWENT;	
<u> </u>		(13 1 - 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2002/00/01
9	12		USPAT;	2003/08/01
		same laminat\$4 same amorphous same	US-PGPUB;	15:26
		(crystalliz\$4 or anneal\$4)	EPO; JPO;	
			DERWENT;	
	1	I and the second se	TRM TOB	1

L Number	Hits	Search Text	DB	Time stamp
-	93	yamazaki.in. and (ge or germanium) same laser same anneal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 16:17
-	118	(ge or germanium) near10 amorphous same (si or silicon) near10 amorphous same anneal\$4 same (crystal\$4 or crystalliz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 16:23
-	4	(ge or germanium) near10 amorphous same (si or silicon) near10 amorphous same anneal\$4 same (crystal\$4 or crystalliz\$4) same (first and second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 16:36
-	21	(ge or germanium) near10 amorphous near5 (first or second) same laser and (si or silicon) near10 amorphous near10 (first or second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 16:54
-	9	(ge or germanium) near10 amorphous near5 (first or second) same anneal\$4 and (si or silicon) near10 amorphous near10 (first or second)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 16:58
-	172	<pre>(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) same (silicon or si) and (ge or germanium) near10 amorphous</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/01 10:47
_	14	<pre>(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) and first near10 (ge or germanium) near10 amorphous</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/01 10:50
-	49	<pre>(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) and (ge or germanium) near10 amorphous and second near10 (film or layer) near10 amorphous near10 (si or silicon)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:20
-	97	<pre>(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) same ((silicon or si) and (ge or germanium))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/01 11:21
-	85	<pre>(shunpei.in. near2 yamazaki.in.) and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) same ((silicon or si) and (ge or germanium)) same amorphous</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/01 11:22
_	18	(semiconductor near2 energy near2 laboratory or sel).as. and laser near3 (crystal\$4 or crystalliz\$4 or anneal\$4) and ((silicon or si) and (ge or germanium)) same amorphous same first same second	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 11:29